

Drift Currents



Thermal Equilibrium

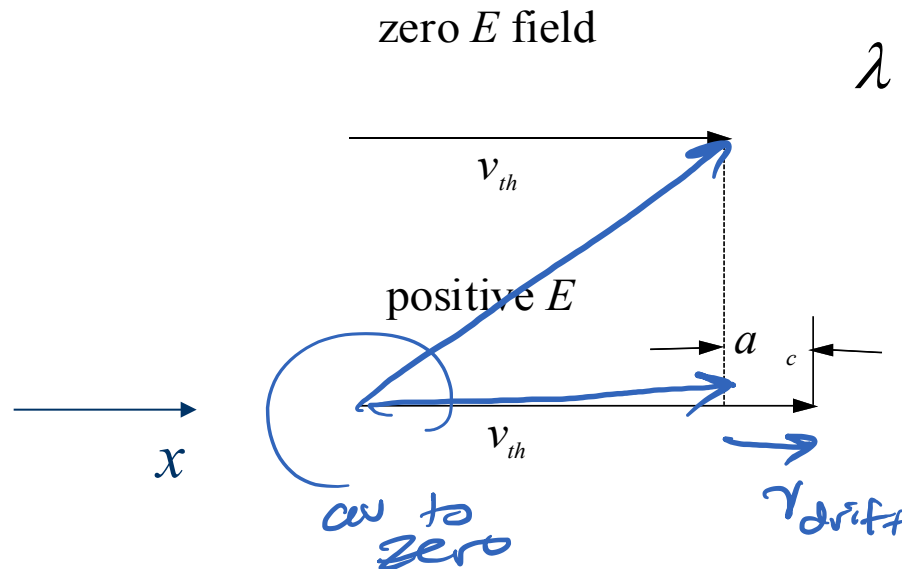
Rapid, random motion of holes and electrons at “thermal velocity” $v_{th} = 10^7$ cm/s with collisions every $\tau_c = 10^{-13}$ s.

$$\frac{1}{2} m_n^* v_{th}^2 = \frac{1}{2} kT$$

Apply an electric field E and charge carriers accelerate ... for τ_c seconds

$$\lambda = v_{th} \tau_c$$

$$\lambda = 10^7 \text{ cm/s} \times 10^{-13} \text{ s} = 10^{-6} \text{ cm}$$



Drift Velocity and Mobility

For holes:

$$v_{dr} = a \cdot \tau_c = \left(\frac{F_e}{m_p} \right) \tau_c = \left(\frac{qE}{m_p} \right) \tau_c = \left(\frac{q \tau_c}{m_p} \right) E$$

Handwritten notes:

- $F = qE$ (circled in blue)
- a is labeled "acceleration" (with a blue arrow pointing to it)
- $\frac{F_e}{m_p}$ is labeled "Force/mass" (with a blue wavy line under it)
- μ_p is labeled "mobility" (with a blue arrow pointing to it)

$$v_{dr} = \mu_p E$$

For electrons:

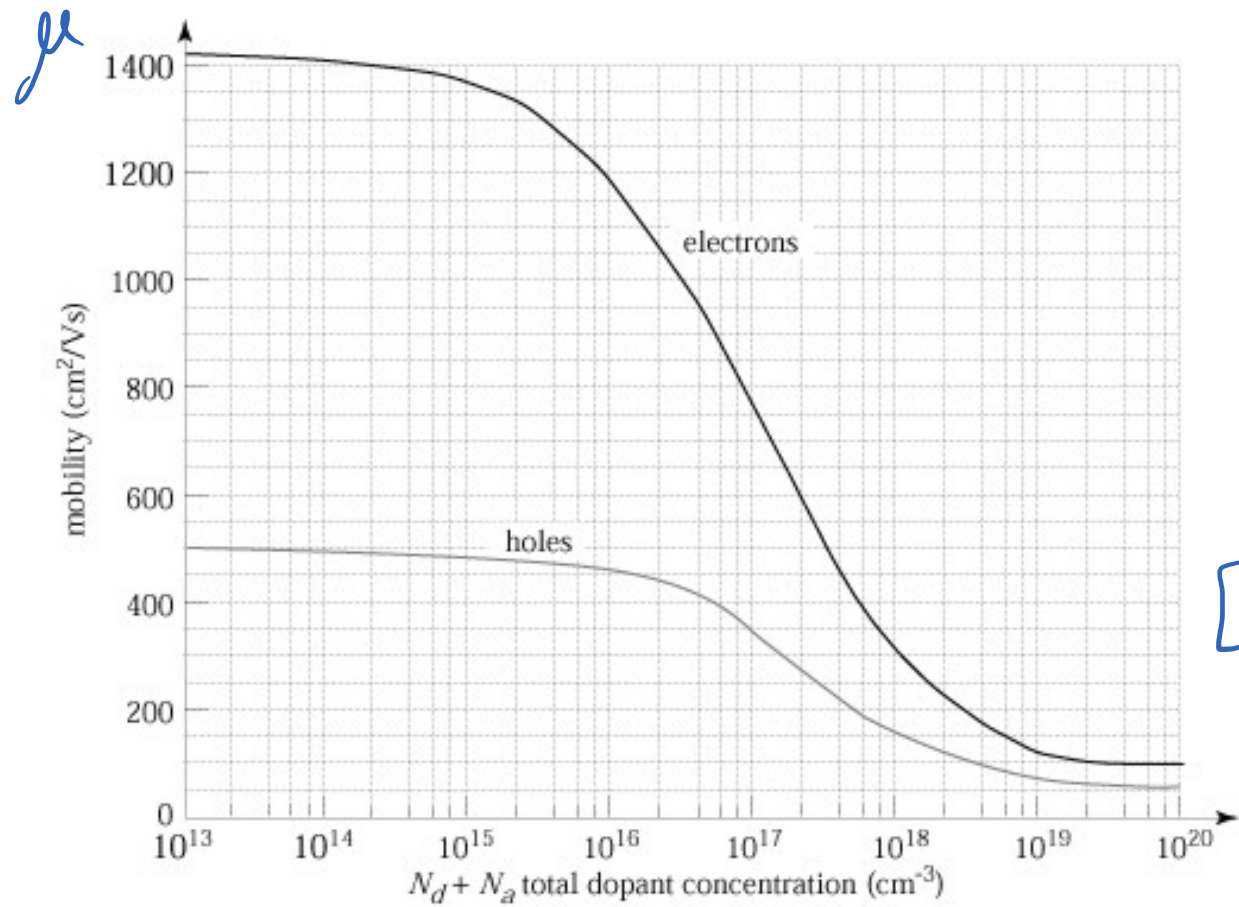
$$v_{dr} = a \cdot \tau_c = \left(\frac{F_e}{m_e} \right) \tau_c = \left(\frac{-qE}{m_e} \right) \tau_c = - \left(\frac{q \tau_c}{m_e} \right) E$$
$$v_{dr} = -\mu_n E$$

Handwritten notes:

- m_e and m_e are circled in red in the electron equation.

Typo

Mobility vs. Doping in Silicon at 300 °K



$v = \mu E$

$\mu = \frac{v}{E}$

$[\mu] = \frac{\text{cm/s}}{\text{V/cm}}$

$= \frac{\text{cm}^2}{\text{V}\cdot\text{s}}$

Typical values:

$N = N_d + N_a$

$\mu_n = 1000$

$\mu_p = 400$

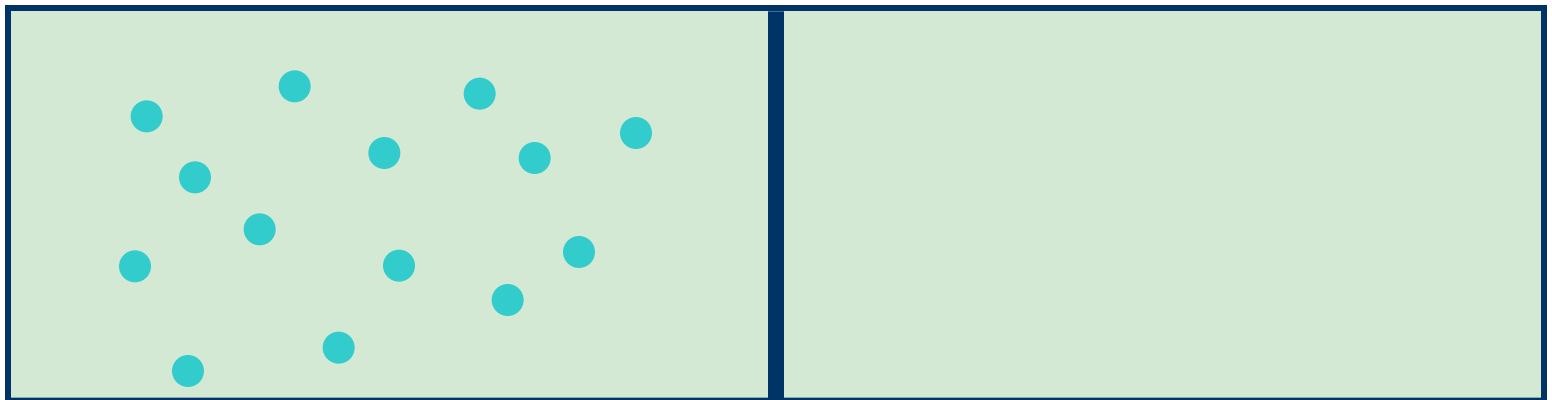
$\mu = \frac{q \tau_c}{m}$

Diffusion Currents



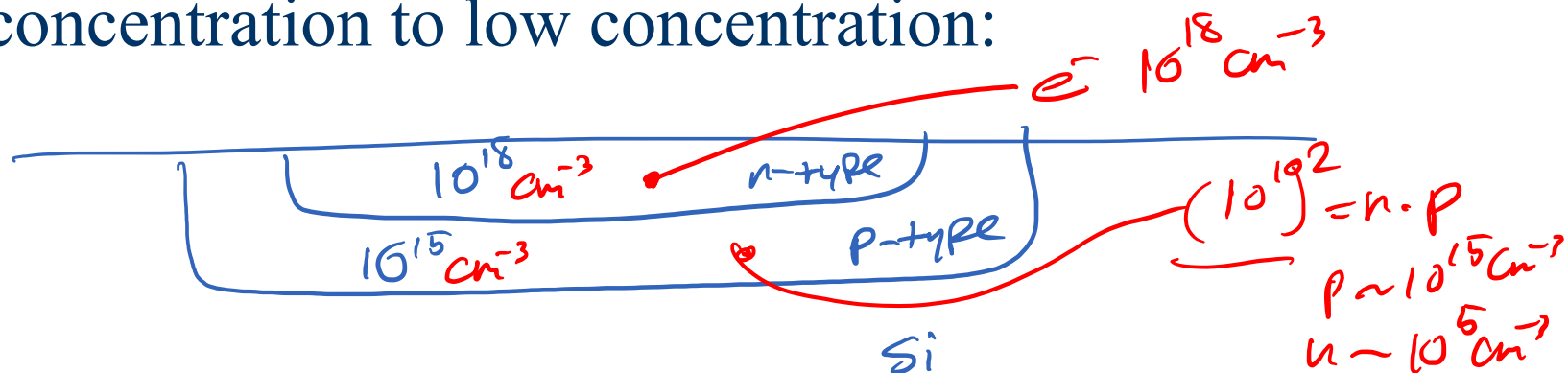
Diffusion

- Diffusion occurs when there exists a concentration gradient
- In the figure below, imagine that we fill the left chamber with a gas at temperature T
- If we suddenly remove the divider, what happens?
- The gas will fill the entire volume of the new chamber. How does this occur?



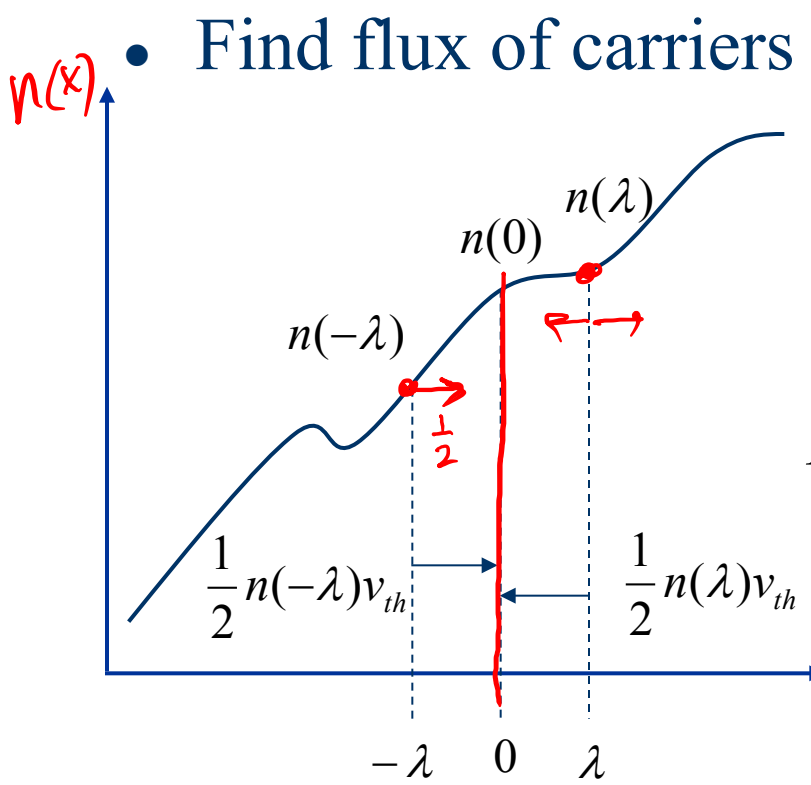
Diffusion (cont)

- The net motion of gas molecules to the right chamber was due to the concentration gradient
- If each particle moves on average left or right then eventually half will be in the right chamber
- If the molecules were charged (or electrons), then there would be a net current flow
- The diffusion current flows from high concentration to low concentration:



Diffusion Equations

- Assume that the mean free path is $\lambda = v_{th} \tau$
- Find flux of carriers crossing $x=0$ plane



$$F = \frac{1}{2} v_{th} (n(-\lambda) - n(\lambda))$$

not due to charge but due to direction

$$F = \frac{1}{2} v_{th} \left(\left[\cancel{n(0)} - \lambda \frac{dn}{dx} \right] - \left[\cancel{n(0)} + \lambda \frac{dn}{dx} \right] \right)$$

$$F = -v_{th} \lambda \frac{dn}{dx}$$

$x(m)$
↑
Spatial

$$J = -qF = q(v_{th} \lambda) \frac{dn}{dx}$$

gradient!

Einstein Relation

- The thermal velocity is given by kT

Thermal energy is driving motion

$$\frac{1}{2} m_n^* v_{th}^2 = \frac{1}{2} kT$$

Mean Free Time

$$\lambda = v_{th} \tau_c$$

time b/w collisions

$$v_{th} \lambda = (v_{th}^2) \tau_c = kT \frac{\tau_c}{m_n^*} = \left(\frac{kT}{q} \right) \left(\frac{q \tau_c}{m_n^*} \right) = \frac{kT}{q} \mu$$

mobility

$$J = q v_{th} \lambda \frac{dn}{dx} = q \left(\frac{kT}{q} \mu_n \right) \frac{dn}{dx}$$

diffusion ("small" currents)

$$D_n = \left(\frac{kT}{q} \right) \mu_n$$

mobility (drift)

25mV

$$J = q D \frac{dn}{dx}$$

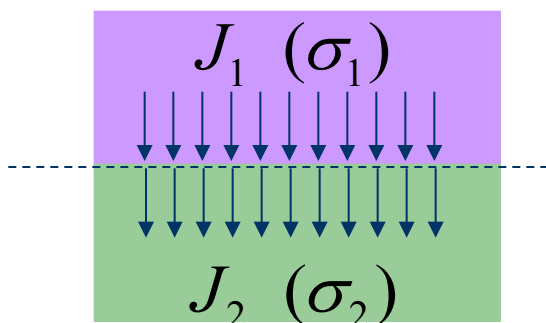
diffusion coefficient

Total Current and Boundary Conditions

- When both drift and diffusion are present, the total current is given by the sum:

$$J = J_{drift} + J_{diff} = q\mu_{n,p}nE + qD_n \frac{dn}{dx} \quad \begin{matrix} \text{electrons} \\ \text{holes} \end{matrix}$$

- In resistors, the carrier is approximately uniform and the second term is nearly zero
- For currents flowing uniformly through an interface (no charge accumulation), the field is discontinuous



$$J_1 = J_2$$

$$\sigma_1 E_1 = \sigma_2 E_2$$

$$\frac{E_1}{E_2} = \frac{\sigma_2}{\sigma_1}$$

Reference

- Edward Purcell, *Electricity and Magnetism*, Berkeley Physics Course Volume 2 (2nd Edition), pages 133-142.